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PRELIMINARY AMENDMENT  
National Stage Entry of PCT/JP03/015415  
Q88348

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AMENDMENTS TO THE CLAIMS

**This listing of claims will replace all prior versions and listings of claims in the application:**

**LISTING OF CLAIMS:**

1. (original): A semiconductor light emitting device comprising:  
a substrate; and  
a light emitting layer, which is provided on the substrate, of a quantum well structure  
including well layers and barrier layers which are composed of Group III nitride semiconductors,  
wherein

an impurity composed of an element in Periodic Table Group 6B is substantially  
uniformly doped in said well layers and said barrier layers.

2. (original): The semiconductor light emitting device according to claim 1, wherein  
a maximum value of a concentration of said impurity doped in said well layers and said  
barrier layers is less than or equal to five times as high as a minimum value of the concentration  
of said impurity.

3. (currently amended): The semiconductor light emitting device according to claim 1 or  
~~claim 2~~, wherein

said substrate is a Group III nitride semiconductor substrate whose surface dislocation  
density is less than  $1 \times 10^8$  cm<sup>-2</sup>.

4. (original): A semiconductor light emitting device comprising:

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a Group III nitride semiconductor substrate whose surface dislocation density is less than  $1 \times 10^8 \text{ cm}^{-2}$ ; and

a light emitting layer, which is provided on the substrate, of a quantum well structure including well layers and barrier layers which are composed of Group III nitride semiconductors, and wherein

said light emitting layer includes an element in Periodic Table Group 6B as an impurity.

5. (currently amended): The semiconductor light emitting device according to ~~any one of~~ claim 1 ~~to claim 4~~, comprising

a semiconductor layer including an element in Periodic Table Group 4B as an impurity between said substrate and said light emitting layer.

6. (currently amended): The semiconductor light emitting device according to ~~any one of~~ claim 1 ~~to claim 5~~, wherein

said element in Periodic Table Group 6B is O or S.

7. (currently amended): The semiconductor light emitting device according to ~~any one of~~ claim 1 ~~to claim 6~~, wherein

said barrier layers include said element in Periodic Table Group 6B, and include regions having an n-type conductive pattern.

8. (currently amended): The semiconductor light emitting device according to ~~any one of~~ claim 1 ~~to claim 7~~, wherein,

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given that a thickness of said light emitting layer is d (nm), an average volume concentration in said light emitting layer of said element in Periodic Table Group 6B is x (cm<sup>-3</sup>), and a number of quantum wells is n, an impurity concentration defined by

$$xd \times 10^{-7}/n$$

is greater than or equal to  $3 \times 10^{11}$  cm<sup>-2</sup>.

9. (currently amended): The semiconductor light emitting device according to ~~any one of~~ claim 1 ~~to claim 8~~, wherein,

given that a thickness of said light emitting layer is d (nm), an average carrier concentration in said light emitting layer is y (cm<sup>-3</sup>), and a number of quantum wells is n, a carrier concentration defined by

$$yd \times 10^{-7}/n \text{ is greater than or equal to } 1.5 \times 10^{10} \text{ cm}^{-2}$$

10. (currently amended): The semiconductor light emitting device according to ~~any one of~~ claim 1 ~~to claim 9~~, wherein

said barrier layers include In.

11. (original): A method of manufacturing a semiconductor light emitting device, comprising

forming a light emitting layer composed of a Group III nitride semiconductors on a substrate by a vapor phase deposition method, by using a doping gas containing an element in Periodic Table Group 6B, and a mixed gas including a Group III precursor gas and a nitrogen source gas, wherein

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a molar flow rate of the doping gas is made excessive more than a molar flow rate of the Group III precursor gas.

12. (original): The method of manufacturing a semiconductor light emitting device according to claim 11, wherein

the step of forming said light emitting layer is executed after forming Group III nitride semiconductor layers containing an element in Periodic Table Group 4B as an impurity on said substrate by a vapor phase deposition method.

13. (original): The method of manufacturing a semiconductor light emitting device according to claim 12, wherein

after forming Group III nitride semiconductor layers containing an element in Periodic Table Group 4B as an impurity, a film-forming gas used for forming the Group III nitride semiconductor layers is purged, and next, said light emitting layer is formed.

14. (currently amended): The method of manufacturing a semiconductor light emitting device according to ~~any one of~~ claim 11 ~~to claim 13~~, wherein

said light emitting layer has a quantum well structure, the step of forming said light emitting layer includes a step of forming well layers and barrier layers alternately, and said doping gas is introduced at the time of forming said barrier layers.

15. (currently amended): The method of manufacturing a semiconductor light emitting device according to ~~any one of~~ claim 11 ~~to claim 14~~, wherein

the element in Periodic Table Group 6B is O or S.